

1.02500 Fairchild Semiconductor International

	PNP High Voltage Ampli (contin							
Electrical Characteristics TA = 25°C unless otherwise noted								
Symbol	Parameter	Test Conditions	Min	Мах	Units			
OFF CHA	RACTERISTICS							
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage*	$I_{\rm C} = 1.0 \text{ mA}, I_{\rm B} = 0$	300		V			
V _{(BR)CBO}	Collector-Base Breakdown Voltage	$I_{\rm C} = 100 \ \mu {\rm A}, \ I_{\rm E} = 0$	300		V			
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_{\rm E} = 100 \ \mu {\rm A}, \ I_{\rm C} = 0$	5.0		V			
I _{CBO}	Collector-Cutoff Current	$V_{CB} = 200 \text{ V}, \text{ I}_{E} = 0$		0.25	μA			
I _{EBO}	Emitter-Cutoff Current	$V_{EB} = 3.0 \text{ V}, \text{ I}_{C} = 0$		0.1	μA			
	ACTERISTICS*							
h _{FE}	DC Current Gain	$I_{C} = 1.0 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 10 \text{ mA}, V_{CE} = 10 \text{ V}$ $I_{C} = 30 \text{ mA}, V_{CE} = 10 \text{ V}$	25 40 25					
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$I_{\rm C} = 20 \text{ mA}, I_{\rm B} = 2.0 \text{ mA}$		0.5	V			
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{\rm C} = 20 \text{ mA}, I_{\rm B} = 2.0 \text{ mA}$		0.9	V			
SMALL S	IGNAL CHARACTERISTICS	$l_{c} = 10 \text{ mA}$, $V_{cr} = 20 \text{ V}$	50		MHz			

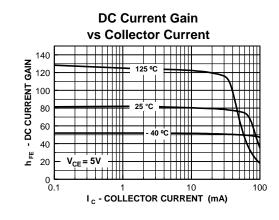
f⊤	Current Gain - Bandwidth Product	$I_{C} = 10 \text{ mA}, V_{CE} = 20 \text{ V},$ f = 100 MHz	50		MHz
C _{cb}	Collector-Base Capacitance	$V_{CB} = 20 \text{ V}, I_E = 0, f = 1.0 \text{ MHz}$		6.0	pF

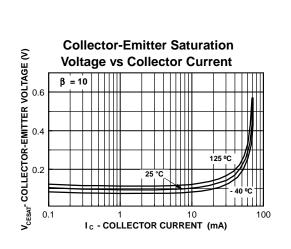
*Pulse Test: Pulse Width \leq 300 µs, Duty Cycle \leq 2.0%

Spice Model

PNP (Is=218.9f Xti=3 Eg=1.11 Vaf=100 Bf=99 Ne=1.307 Ise=218.9f Ikf=.2016 Xtb=1.5 Br=24.67 Nc=2 Isc=0 Ikr=0 Rc=7 Cjc=19.88p Mjc=.4876 Vjc=.75 Fc=.5 Cje=81.49p Mje=.3493 Vje=.75 Tr=516.9p Tf=1.395n Itf=1.5 Vtf=22 Xtf=270 Rb=10)

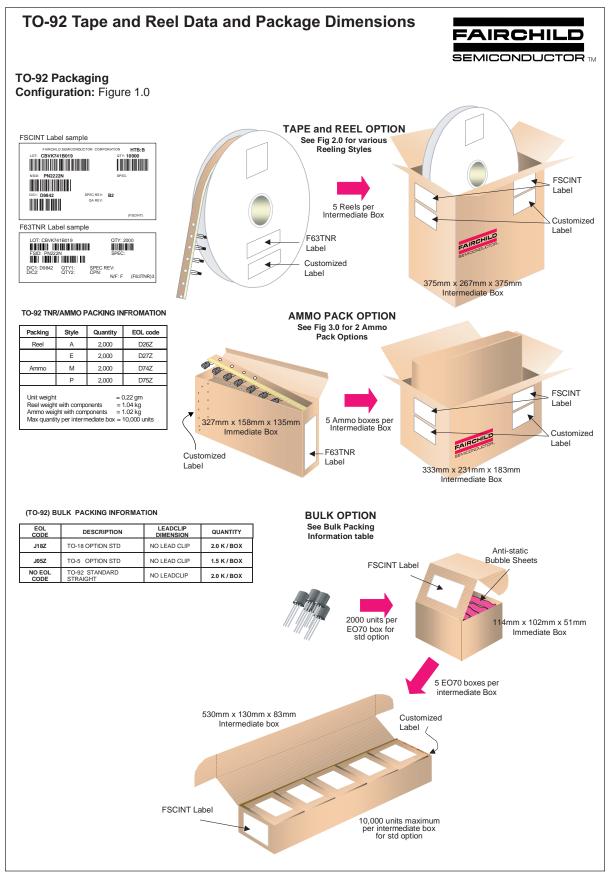




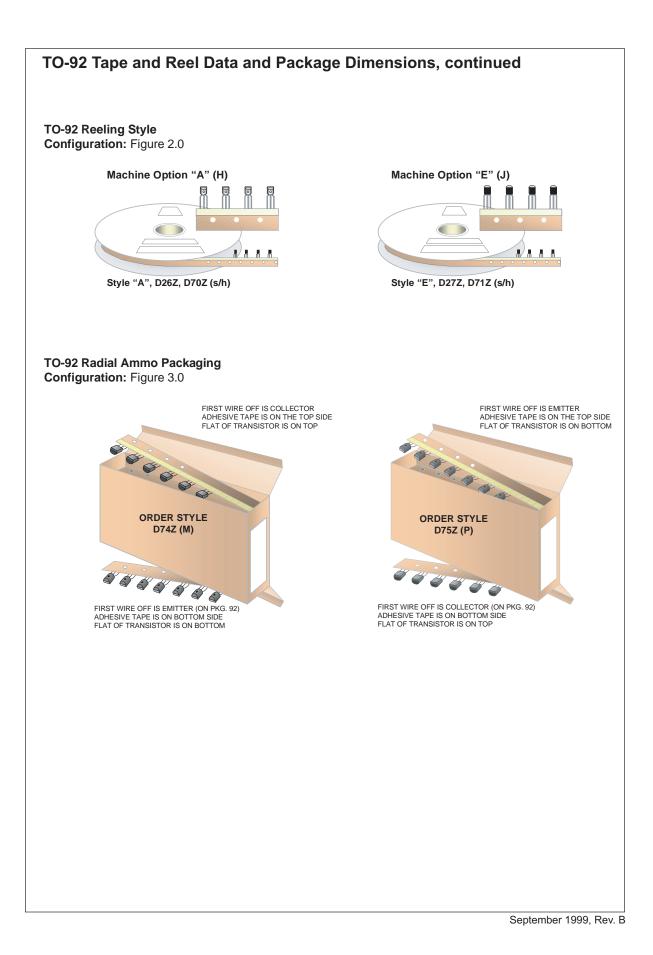


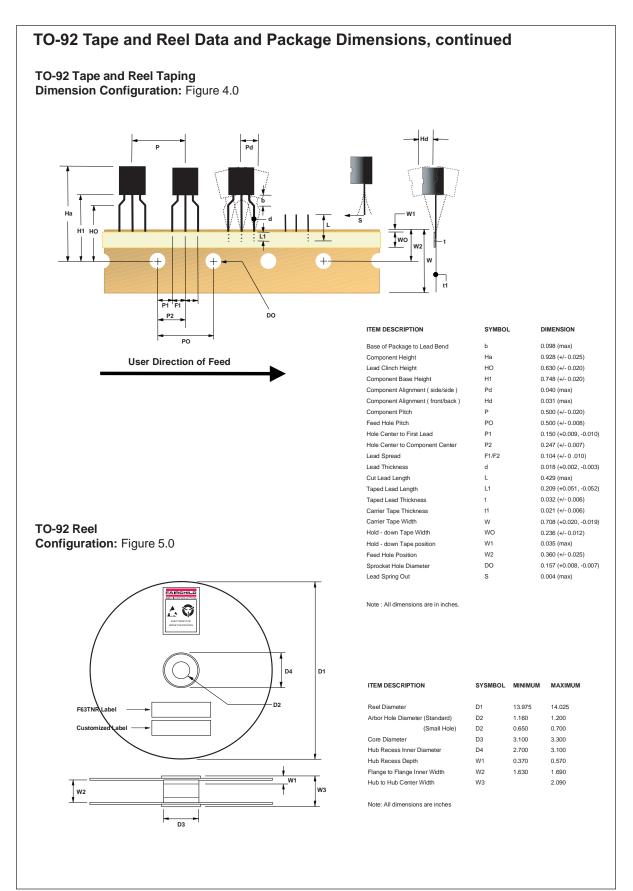
PNP High Voltage Amplifier (continued) Typical Characteristics (continued) **Base-Emitter Saturation Base-Emitter ON Voltage vs** Voltage vs Collector Current **Collector Current** ċ 25 25 125 125 °C $V_{CE} = 5V$ 10 П 10 I_c - COLLECTOR CURRENT (mA) 100 10 I _c - COLLECTOR CURRENT (mA) 1 100 **Collector-Cutoff Current Junction Capacitance** vs Reverse Bias Voltage vs Ambient Temperature 10 JUNCTION CAPACITANCE (pF) f = 1.0 MHz /_{CB}= 150V C ib 1 0.1 – 0.1 1 10 V _R - REVERSE VOLTAGE (V) 100 25 50 75 100 125 150 TA - AMBIENT TEMPERATURE (°C) **Power Dissipation vs Gain Bandwidth Product Ambient Temperature** vs Collector Current $f_{\rm T}$ - GAIN BANDWIDTH PRODUCT (MHz) 100 V_{CE} = 50V 0.75 0.5 0.25 **°** SOT-223 80 TO-92 V_{CE} = 15V 60 SOT-23 40 20 0 L 0 0 50 75 100 TEMPERATURE (°C) 25 125 10 20 I c - COLLECTOR CURRENT (mA) 150 1 50 100

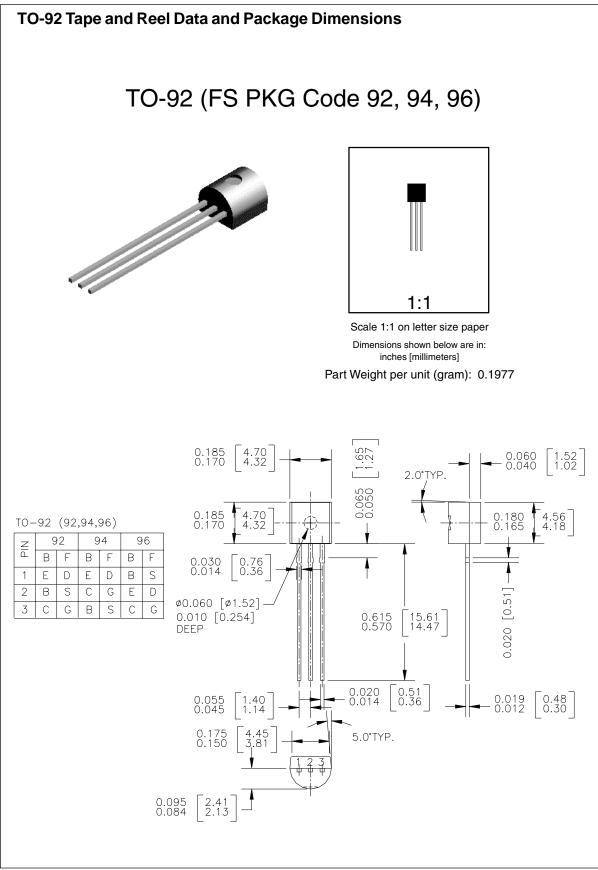
MPSA92 / MMBTA92 / PZTA92



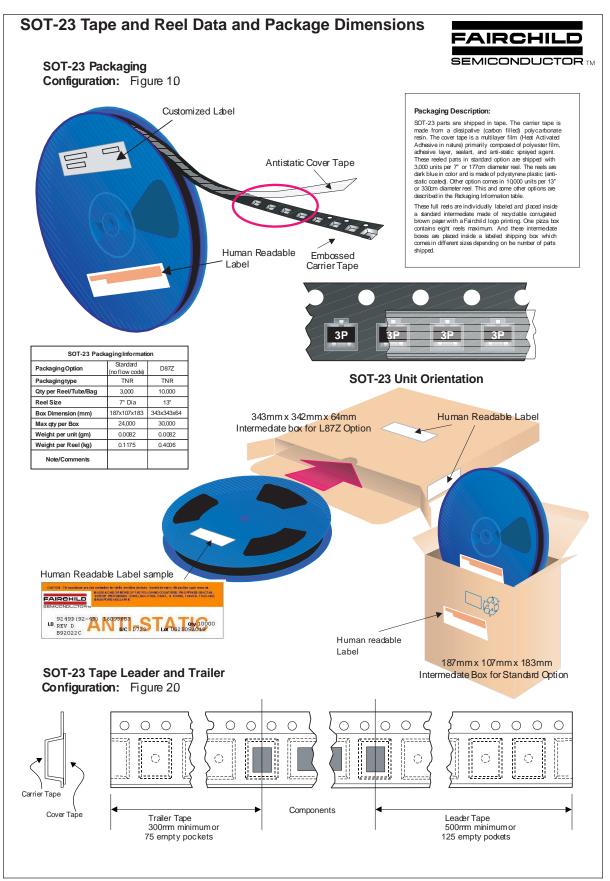
September 1999, Rev. B

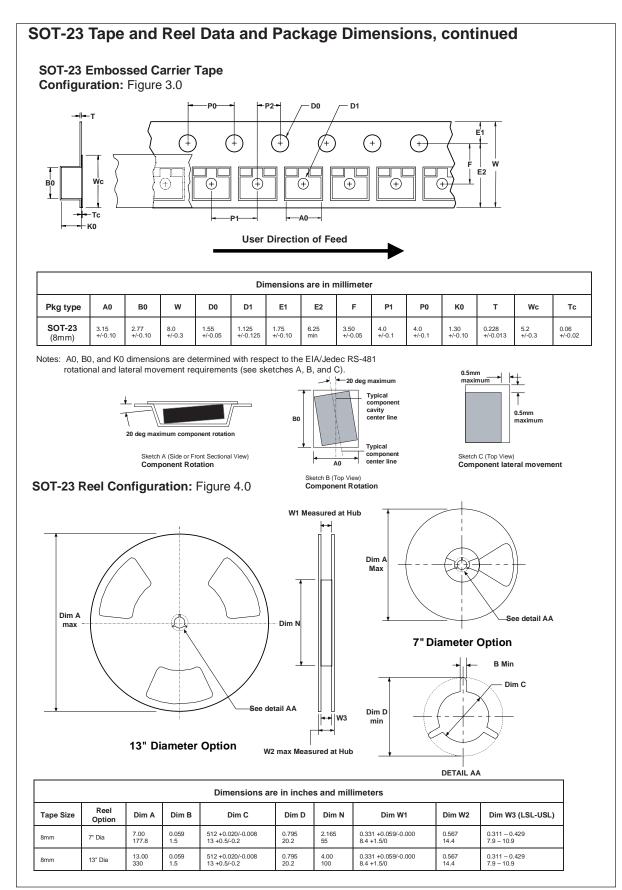


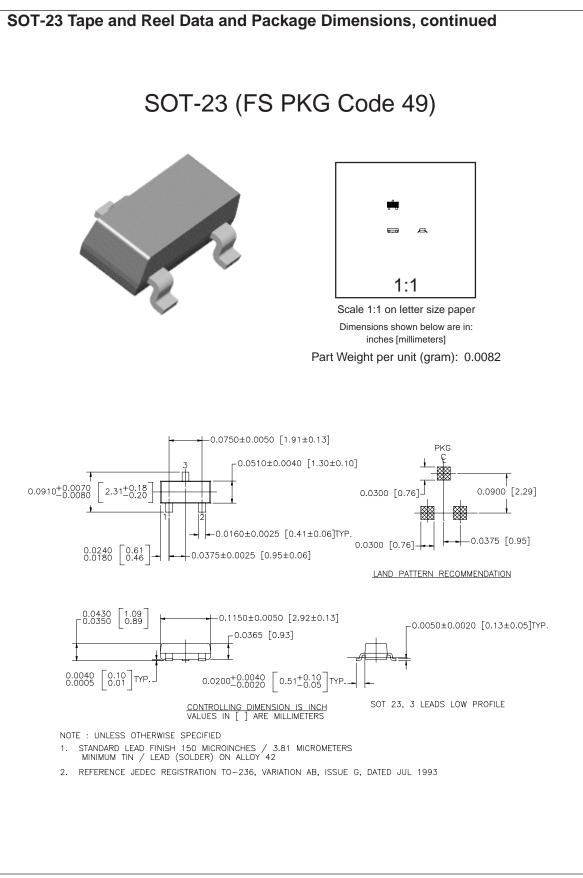




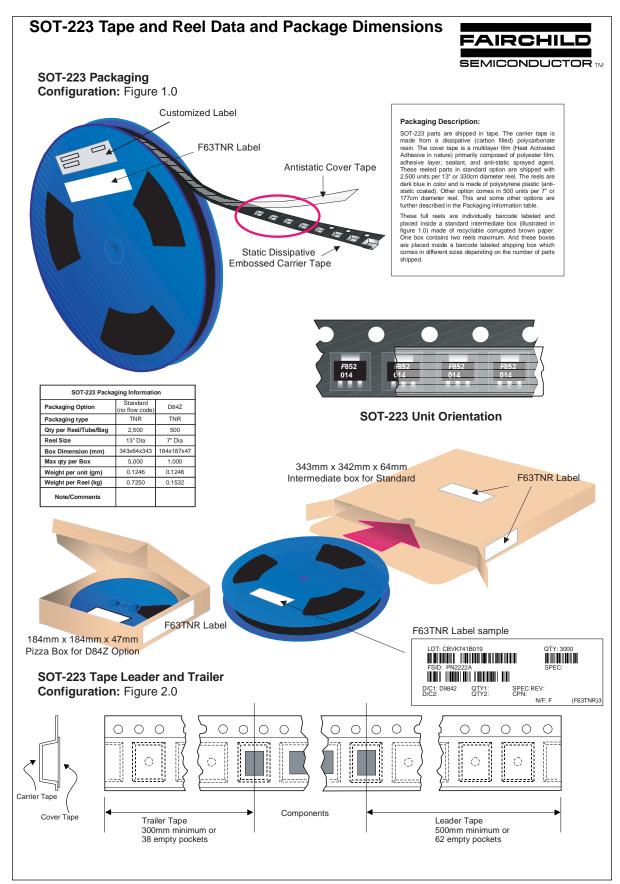
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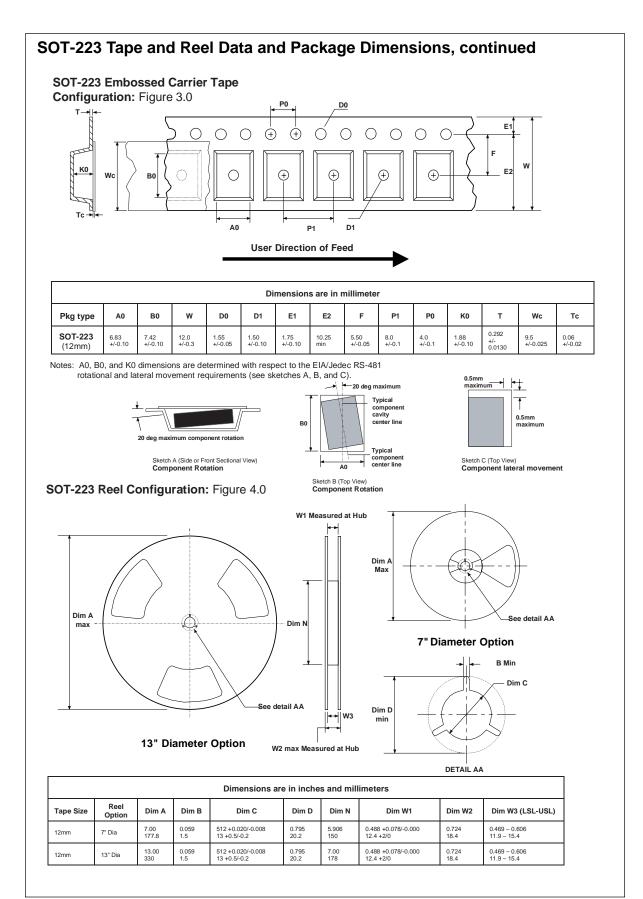


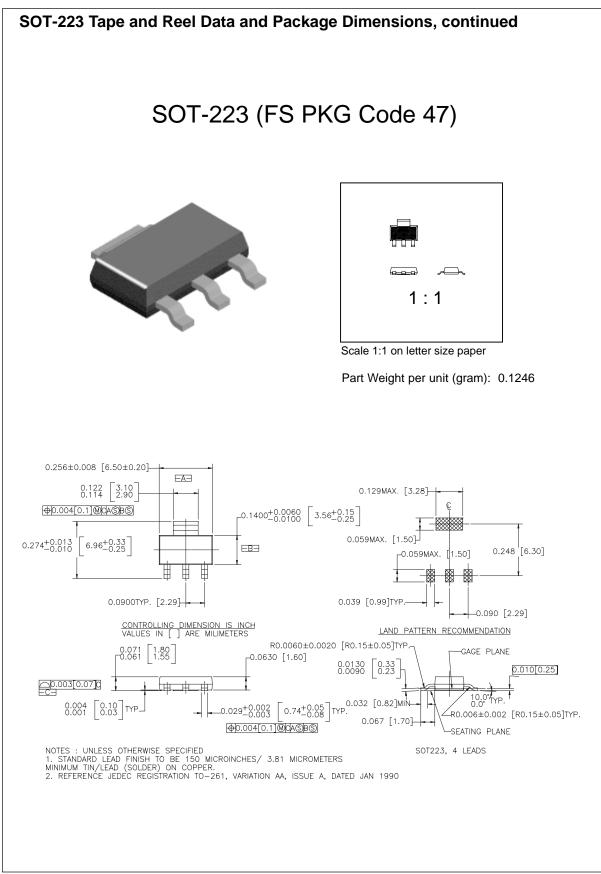




September 1998, Rev. A1







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